Laurence Eaves

List of Publications by Year
in descending order

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456 papers	16,942 citations	28190 55 h-index	18606 119 g-index
459 all docs	459 docs citations	459 times ranked	13997 citing authors

#	Article	IF	Citations
1	Exciton and Phonon Radiative Linewidths in Monolayer Boron Nitride. Physical Review X, 2022, 12, .	2.8	5
2	Heavy carrier effective masses in van der Waals semiconductor Sn(SeS) revealed by high magnetic fields up to 150 T. Physical Review B, 2021, 104, .	1.1	1
3	Grapheneâ€™s non-equilibrium fermions reveal Doppler-shifted magnetophonon resonances accompanied by Mach supersonic and Landau velocity effects. Nature Communications, 2021, 12, 6392.	5.8	5
4	Van der Waals SnSe 2(1â^' x) S 2 x Alloys: Compositionâ€Dependent Bowing Coefficient and Electronâ€“Phonon Interaction. Advanced Functional Materials, 2020, 30, 1908092.	7.8	18
5	Defect-Assisted High Photoconductive UVâ€“Visible Gain in Perovskite-Decorated Graphene Transistors. ACS Applied Electronic Materials, 2020, 2, 147-154.	2.0	13
6	Resonant tunnelling into the two-dimensional subbands of InSe layers. Communications Physics, 2020, 3, .	2.0	22
7	Two-Dimensional Covalent Crystals by Chemical Conversion of Thin van der Waals Materials. Nano Letters, 2019, 19, 6475-6481.	4.5	32
8	Strong magnetophonon oscillations in extra-large graphene. Nature Communications, 2019, 10, 3334.	5.8	25
9	Magnetophonon spectroscopy of Dirac fermion scattering by transverse and longitudinal acoustic phonons in graphene. Physical Review B, 2019, 100, .	1.1	16
10	Direct band-gap crossover in epitaxial monolayer boron nitride. Nature Communications, 2019, 10, 2639.	5.8	162
11	Photoquantum Hall Effect and Lightâ€Induced Charge Transfer at the Interface of Graphene/InSe Heterostructures. Advanced Functional Materials, 2019, 29, 1805491.	7.8	20
12	High-order fractal states in graphene superlattices. Proceedings of the National Academy of Sciences of the United States of America, 2018, 115, 5135-5139.	3.3	63
13	High-temperature molecular beam epitaxy of hexagonal boron nitride layers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	0.6	31
14	Lattice-Matched Epitaxial Graphene Grown on Boron Nitride. Nano Letters, 2018, 18, 498-504.	4.5	39
15	Tunnel spectroscopy of localised electronic states in hexagonal boron nitride. Communications Physics, 2018, 1, .	2.0	33
16	High-Temperature Molecular Beam Epitaxy of Hexagonal Boron Nitride with High Active Nitrogen Fluxes. Materials, 2018, 11, 1119.	1.3	17
17	Magnon-assisted tunnelling in van der Waals heterostructures based on CrBr3. Nature Electronics, 2018, 1, 344-349.	13.1	239
18	MoirÃ©-Modulated Conductance of Hexagonal Boron Nitride Tunnel Barriers. Nano Letters, 2018, 18, 4241-4246.	4.5	19

#	Article	IF	Citations
19	Giant Quantum Hall Plateau in Graphene Coupled to an InSe van der Waals Crystal. Physical Review Letters, 2017, 119, 157701.	2.9	44
20	An atomic carbon source for high temperature molecular beam epitaxy of graphene. Scientific Reports, 2017, 7, 6598.	1.6	16
21	High-temperature quantum oscillations caused by recurring Bloch states in graphene superlattices. Science, 2017, 357, 181-184.	6.0	117
22	High electron mobility, quantum Hall effect and anomalous optical response in atomically thin InSe. Nature Nanotechnology, 2017, 12, 223-227.	15.6	996
23	Hexagonal Boron Nitride Tunnel Barriers Grown on Graphite by High Temperature Molecular Beam Epitaxy. Scientific Reports, 2016, 6, 34474.	1.6	60
24	High temperature MBE of graphene on sapphire and hexagonal boron nitride flakes on sapphire. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	0.6	22
25	The direct-to-indirect band gap crossover in two-dimensional van der Waals Indium Selenide crystals. Scientific Reports, 2016, 6, 39619.	1.6	150
26	Strain-Engineered Graphene Grown on Hexagonal Boron Nitride by Molecular Beam Epitaxy. Scientific Reports, 2016, 6, 22440.	1.6	49
27	Resonant Zener tunnelling via zero-dimensional states in a narrow gap diode. Scientific Reports, 2016, 6, 32039.	1.6	4
28	Tuning the valley and chiral quantum state of Dirac electrons in van der Waals heterostructures. Science, 2016, 353, 575-579.	6.0	88
29	Phonon-Assisted Resonant Tunneling of Electrons in Grapheneâ€“Boron Nitride Transistors. Physical Review Letters, 2016, 116, 186603.	2.9	78
30	The apparent fine-tuning of the cosmological, gravitational and fine structure constants. Physica A: Statistical Mechanics and Its Applications, 2016, 443, 355-357.	1.2	3
31	High Broadâ€Band Photoresponsivity of Mechanically Formed InSeâ€“Graphene van der Waals Heterostructures. Advanced Materials, 2015, 27, 3760-3766.	11.1	320
32	Ligandâ€Induced Control of Photoconductive Gain and Doping in a Hybrid Grapheneâ€“Quantum Dot Transistor. Advanced Electronic Materials, 2015, 1, 1500062.	2.6	59
33	Monte Carlo Study on Anomalous Carrier Diffusion in Inhomogeneous Semiconductors. Journal of Physics: Conference Series, 2015, 647, 012059.	0.3	0
34	Resonant tunnelling between the chiral Landau states of twisted graphene lattices. Nature Physics, 2015, 11, 1057-1062.	6.5	64
35	Graphene-hexagonal boron nitride resonant tunneling diodes as high-frequency oscillators. Applied Physics Letters, 2015, 107, .	1.5	58
36	Room Temperature Electroluminescence from Mechanically Formed van der Waals IIIâ€“VI Homojunctions and Heterojunctions. Advanced Optical Materials, 2014, 2, 1064-1069.	3.6	71

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37	Quantum confined acceptors and donors in InSe nanosheets. Applied Physics Letters, 2014, 105, 221909.	1.5	58
38	Quantum oscillations in the photocurrent of GaAs/AlAsp-i-ndiodes. Physical Review B, 2014, 89, .	1.1	11
39	Impact ionization and large room-temperature magnetoresistance in micron-sized high-mobility InAs channels. Physical Review B, 2014, 90, .	1.1	6
40	Twist-controlled resonant tunnelling in graphene/boron nitride/graphene heterostructures. Nature Nanotechnology, 2014, 9, 808-813.	15.6	435
41	Nonequilibrium green function simulations of graphene-nanoribbon resonant-tunneling transistors. Japanese Journal of Applied Physics, 2014, 53, 04EN04.	0.8	4
42	Tuning the Bandgap of Exfoliated InSe Nanosheets by Quantum Confinement. Advanced Materials, 2013, 25, 5714-5718.	11.1	512
43	Meristematic cell proliferation and ribosome biogenesis are decoupled in diamagnetically levitated Arabidopsis seedlings. BMC Plant Biology, 2013, 13, 124.	1.6	33
44	Vertical field-effect transistor based on grapheneâ€“WS2 heterostructures for flexible and transparent electronics. Nature Nanotechnology, 2013, 8, 100-103.	15.6	1,543
45	Resonant tunnelling and negative differential conductance in graphene transistors. Nature Communications, 2013, 4, 1794.	5.8	542
46	Field-effect control of tunneling barrier height by exploiting graphene's low density of states. Journal of Applied Physics, 2013, 113, .	1.1	35
47	Theory of Resonant Tunneling through a Donor State. Japanese Journal of Applied Physics, 2012, 51, 02BJ02.	0.8	0
48	Laser Location and Manipulation of a Single Quantum Tunneling Channel in an InAs Quantum Dot. Physical Review Letters, 2012, 108, 117402.	2.9	14
49	Probing the sensitivity of electron wave interference to disorder-induced scattering in solid-state devices. Physical Review B, 2012, 85, .	1.1	8
50	Nanoengineering the built-in electric field of a photonic device by interstitial-ion diffusion. Physical Review B, 2012, 85, .	1.1	0
51	Effect of magnetically simulated zero-gravity and enhanced gravity on the walk of the common fruitfly. Journal of the Royal Society Interface, 2012, 9, 1438-1449.	1.5	16
52	Subterahertz Acoustical Pumping of Electronic Charge in a Resonant Tunneling Device. Physical Review Letters, 2012, 108, 226601.	2.9	33
53	Shape oscillations of an electrically charged diamagnetically levitated droplet. Applied Physics Letters, 2012, 100, 114106.	1.5	8
54	Microgravity simulation by diamagnetic levitation: effects of a strong gradient magnetic field on the transcriptional profile of Drosophila melanogaster. BMC Genomics, 2012, 13, 52.	1.2	47

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55	Field-Effect Tunneling Transistor Based on Vertical Graphene Heterostructures. Science, 2012, 335, 947-950.	6.0	2,268
56	Addendum to â€œVibrations of a diamagnetically levitated water dropletâ€• Physical Review E, 2012, 85, 017301.	0.8	3
57	Linear magnetoresistance due to multiple-electron scattering by low-mobility islands in an inhomogeneous conductor. Nature Communications, 2012, 3, 1097.	5.8	76
58	Electron Tunneling through Ultrathin Boron Nitride Crystalline Barriers. Nano Letters, 2012, 12, 1707-1710.	4.5	724
59	Cyclotron resonance mass and Fermi energy pinning in the In(AsN) alloy. Applied Physics Letters, 2011, 98, .	1.5	11
60	Magnetic Field Modulated Photoreflectance Study of the Electron Effective Mass in Dilute Nitride Semiconductors. AIP Conference Proceedings, 2011, , .	0.3	3
61	Ultrafast Acoustic Gating of Photocurrent in Nanodevices With a Quantum Well. AIP Conference Proceedings, 2011, , .	0.3	0
62	Electronic energy levels, wavefunctions and potential landscape of nanostructures probed by magneto-tunnelling spectroscopy. Journal of Physics: Conference Series, 2011, 334, 012010.	0.3	0
63	TEM of Nano-LEDs made by laser writing. Journal of Physics: Conference Series, 2011, 326, 012055.	0.3	1
64	Picosecond strain pulses probed by the photocurrent in semiconductor devices with quantum wells. Physical Review B, 2011, 83, .	1.1	11
65	Diamagnetic levitation enhances growth of liquid bacterial cultures by increasing oxygen availability. Journal of the Royal Society Interface, 2011, 8, 334-344.	1.5	30
66	Diamagnetic levitation enhances growth of liquid bacterial cultures by increasing oxygen availability. Nature Precedings, 2010, , .	0.1	1
67	Manipulating and Imaging the Shape of an Electronic Wave Function by Magnetotunneling Spectroscopy. Physical Review Letters, 2010, 105, 236804.	2.9	18
68	Microscopic Analysis of the Valence Band and Impurity Band Theories of (Ga,Mn)As. Physical Review Letters, 2010, 105, 227202.	2.9	36
69	Hot electron transport and impact ionization in the narrow energy gap InAs1â^'xNx alloy. Applied Physics Letters, 2010, 96, 052115.	1.5	7
70	Optical Imaging of Electrical Carrier Injection into Individual InAs Quantum Dots. Physical Review Letters, 2010, 105, 257401.	2.9	6
71	Using randomly distributed charges to create quantum dots. Physical Review B, 2010, 81, .	1.1	11
72	Nanoscale Potential Fluctuations in (GaMn)As/GaAs Heterostructures: From Individual Ions to Charge Clusters and Electrostatic Quantum Dots. Nano Letters, 2010, 10, 4874-4879.	4.5	6

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73	Vibrations of a diamagnetically levitated water droplet. Physical Review E, 2010, 81, 056312.	0.8	41
74	Ultrafast acoustical gating of the photocurrent in apâ”iâ”ntunneling diode incorporating a quantum well. Physical Review B, 2009, 80, .	1.1	7
75	Effect of low nitrogen concentrations on the electronic properties of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>InAs</mml:mtext></mml:mrow><mml:mrow><mml:mn>1</mml:mn> Physical Review B, 2009, 80, .	1.1	27
76	Sensitive detection of photoexcited carriers by resonant tunneling through a single quantum dot. Physical Review B, 2009, 79, .	1.1	9
77	Tailoring the electrical conductivity of GaAs by nitrogen incorporation. Journal of Physics Condensed Matter, 2009, 21, 174209.	0.7	4
78	Carrier injection effects on exciton dynamics in GaAs/AlAs resonant-tunneling diodes. Europhysics Letters, 2009, 85, 67010.	0.7	4
79	Resonant tunneling through a dilute nitride quantum well. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 198-202.	0.8	0
80	Electron effective mass and mobility in heavily doped n-GaAsN probed by Raman scattering. Journal of Applied Physics, 2008, 103, 103528.	1.1	17
81	Nonaxisymmetric Shapes of a Magnetically Levitated and Spinning Water Droplet. Physical Review Letters, 2008, 101, 234501.	2.9	68
82	Fock-Darwin-Like Quantum Dot States Formed by Charged Mn Interstitial Ions. Physical Review Letters, 2008, 101, 226807.	2.9	19
83	Introduction. Carbon-based electronics: fundamentals and device applications. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2008, 366, 189-193.	1.6	25
84	Electron coherence length and mobility in highly mismatched III-N-V alloys. Applied Physics Letters, 2008, 93, .	1.5	17
85	High field electron dynamics in dilute nitride Ga(AsN). Applied Physics Letters, 2008, 93, .	1.5	7
86	Upconversion electroluminescence in InAs quantum dot light-emitting diodes. Applied Physics Letters, 2008, 92, .	1.5	22
87	Electron effective mass and Si-donor binding energy inGaAs1â”xNxprobed by a high magnetic field. Physical Review B, 2008, 77, .	1.1	13
88	Bifurcations and chaos in semiconductor superlattices with a tilted magnetic field. Physical Review E, 2008, 77, 026209.	0.8	27
89	PROBING THE SCATTERING POTENTIAL OF N-IMPURITIES IN GaAs BY MAGNETO-TUNNELING. International Journal of Modern Physics B, 2007, 21, 1600-1604.	1.0	0
90	Magnetoanisotropy of electron-correlation-enhanced tunneling through a quantum dot. Physical Review B, 2007, 75, .	1.1	20

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91	Measuring the hole chemical potential in ferromagnetic Ga1âˆ'xMnxAsâˆ•GaAs heterostructures by photoexcited resonant tunneling. Applied Physics Letters, 2007, 90, 082106.	1.5	12
92	Magnetic-field-induced miniband conduction in semiconductor superlattices. Physical Review B, 2007, 76, .	1.1	15
93	Magnetophonon oscillations in the negative differential conductance of dilute nitrideGaAs1âˆ'xNxsubmicron diodes. Physical Review B, 2007, 75, .	1.1	12
94	Magnetic field tuning of hot electron resonant capture in a semiconductor device. Applied Physics Letters, 2007, 91, 142104.	1.5	5
95	Character of states near the Fermi level in (Ga,Mn)As: Impurity to valence band crossover. Physical Review B, 2007, 76, .	1.1	139
96	Alignment of Aromatic Peptide Tubes in Strong Magnetic Fields. Advanced Materials, 2007, 19, 4474-4479.	11.1	87
97	One-electron spin-dependent transport in split-gate structures containing self-organized InAs quantum dots. Journal of Experimental and Theoretical Physics, 2007, 105, 145-148.	0.2	1
98	Magnetic-field-induced Fermi-edge singularity in the tunneling current through an InAs self-assembled quantum dot. Journal of Experimental and Theoretical Physics, 2007, 105, 152-154.	0.2	4
99	Observation of the low-temperature peak in the interlayer tunneling conductance in bilayer electron systems in the absence of the magnetic field. Journal of Experimental and Theoretical Physics, 2007, 105, 177-180.	0.2	1
100	Bose condensation of excitons in two-layer electronic systems in the absence of magnetic field. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1120-1123.	0.1	0
101	Single-electron spin-dependent transport in split-gate structures containing self-assembled quantum dots. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1124-1126.	0.1	0
102	Magnetic-field-induced Fermi-edge singularity in the tunnelling current through a self-assembled InAs quantum dot. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1127-1129.	0.1	0
103	Sharp Electroluminescence Lines Excited by Tunneling Injection Into a Large Ensemble of Quantum Dots. AIP Conference Proceedings, 2007, , .	0.3	0
104	Electric-field inversion asymmetry: Rashba and Stark effects for holes in resonant tunneling devices. Physical Review B, 2006, 74, .	1.1	23
105	Raman scattering in InAsâˆ•(AlGa)As self-assembled quantum dots: Evidence of Al intermixing. Applied Physics Letters, 2006, 88, 141905.	1.5	19
106	An empire of many dimensions. Nature Materials, 2006, 5, 775-776.	13.3	2
107	Magnetotunneling spectroscopy of ring-shaped (InGa)As quantum dots: Evidence of excited states with 2pz character. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 57-60.	1.3	0
108	Effect of inter-miniband tunneling on current resonances due to the formation of stochastic conduction networks in superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 285-288.	1.3	11

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109	Anomalous quantum Hall effect induced by nearby quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 148-151.	1.3	0
110	Optical study of resonant states in GaN x As1â^'x. Semiconductors, 2006, 40, 1162-1164.	0.2	0
111	Strong Effect of Resonant Impurities on Landau-Level Quantization. Physical Review Letters, 2006, 96, 236802.	2.9	9
112	Probing the intermixing in In(Ga)Asâ•GaAs self-assembled quantum dots by Raman scattering. Journal of Applied Physics, 2006, 99, 043501.	1.1	19
113	Terahertz response of hot electrons in dilute nitride Ga(AsN) alloys. Applied Physics Letters, 2006, 88, 032107.	1.5	33
114	Modifying the electronic properties of GaAsâ•AlAs superlattices with low-density nitrogen doping. Journal of Applied Physics, 2006, 100, 063718.	1.1	7
115	Voltage-controlled hole spin injection in nonmagneticGaAsâ•AlAsresonant tunneling structures. Physical Review B, 2006, 73, .	1.1	21
116	Sharp-line electroluminescence from individual quantum dots by resonant tunneling injection of carriers. Applied Physics Letters, 2006, 89, 092106.	1.5	8
117	Current flow and energy dissipation in low-dimensional semiconductor superlattices. Applied Physics Letters, 2006, 88, 052111.	1.5	12
118	Stochastic Carrier Dynamics in Semiconductor Superlattices. Acta Physica Polonica A, 2006, 109, 43-52.	0.2	0
119	Charge buildup effects in asymmetric p-type resonant tunneling diodes. Microelectronics Journal, 2005, 36, 356-358.	1.1	0
120	Electrical characterisation of (Ga,Mn,Cr)As thin films grown by molecular beam epitaxy. Journal of Crystal Growth, 2005, 278, 695-698.	0.7	2
121	Transport properties of gated sub-micron mesas incorporating InAs self-assembled quantum dots that conduct near zero bias. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 482-485.	1.3	2
122	Excited states of ring-shaped (InGa)As quantum dots in aGaAsâ•(AlGa)Asquantum well. Physical Review B, 2005, 72, .	1.1	13
123	Trion formation in narrow GaAs quantum well structures. Physical Review B, 2005, 71, .	1.1	19
124	The resonant tunneling of holes through double-barrier structures with InAs QDs at the center of a GaAs quantum well. Semiconductors, 2005, 39, 543-546.	0.2	0
125	Coulomb Oscillations of the Current through Spin-Nondegenerate p States of InAs Quantum Dots. JETP Letters, 2005, 82, 526.	0.4	0
126	Dilute Nitride Ga(AsN) Alloys: an Unusual Band Structure Probed by Magneto-Tunneling. AIP Conference Proceedings, 2005, , .	0.3	0

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127	Electrical conduction properties of Ga(AsN) layers. AIP Conference Proceedings, 2005, , .	0.3	1
128	Observation of current resonances due to enhanced electron transport through stochastic webs in superlattices. AIP Conference Proceedings, 2005, , .	0.3	0
129	Raman scattering by LO phonon-plasmon coupled modes in heavily doped Ga(AsN). AIP Conference Proceedings, 2005, , .	0.3	0
130	Breakup of the conduction band structure of diluteGaAs1âˆ’yNyalloys. Physical Review B, 2005, 71, .	1.1	40
131	Hot-electrons and negative differential conductance inGaAs1âˆ’xNx. Physical Review B, 2005, 72, .	1.1	28
132	Effect of hydrostatic pressure on the fragmented conduction band structure of dilute Ga(AsN) alloys. Physical Review B, 2005, 72, .	1.1	20
133	Quasiballistic transport of hot holes in GaAs submicron channels. Applied Physics Letters, 2005, 86, 042101.	1.5	1
134	Spin splitting of X-valley-related donor impurity states in an AlAs barrier. Physical Review B, 2005, 71, .	1.1	10
135	Cryogenically enhanced magneto-Archimedes levitation. New Journal of Physics, 2005, 7, 118-118.	1.2	40
136	RESONANT TRANSPORT IN SEMICONDUCTOR SUPERLATTICES IN A TILTED MAGNETIC FIELD. , 2005, , .		0
137	The unusual conduction band structure of Ga(AsN) probed by magneto-tunnelling and photocurrent spectroscopy. Journal of Physics Condensed Matter, 2004, 16, S3171-S3185.	0.7	4
138	Exploring the limits of superlattice miniband engineering using inverse scattering. Semiconductor Science and Technology, 2004, 19, S91-S93.	1.0	0
139	Magnetic-Field-Induced Suppression of Electronic Conduction in a Superlattice. Physical Review Letters, 2004, 93, 146801.	2.9	13
140	Electron conduction in two-dimensionalGaAs1âˆ’yNychannels. Physical Review B, 2004, 69, .	1.1	31
141	Time-resolved photoluminescence of InAs quantum dots in a GaAs quantum well. Applied Physics Letters, 2004, 84, 3046-3048.	1.5	23
142	Magnetophotoluminescence study of the influence of substrate orientation and growth interruption on the electronic properties of InAsâ•GaAs quantum dots. Journal of Applied Physics, 2004, 96, 2535-2539.	1.1	13
143	Carrier kinetics in a high-optically efficient quantum dot structure. Semiconductor Science and Technology, 2004, 19, S282-S284.	1.0	3
144	RESONANT TRANSPORT IN SEMICONDUCTOR SUPERLATTICES IN A TILTED MAGNETIC FIELD. International Journal of Modern Physics B, 2004, 18, 3617-3620.	1.0	1

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145	FURTHER EVIDENCE FOR A COLLAPSE OF THE EXCHANGE-ENHANCED SPIN SPLITTING IN TWO DIMENSIONAL SYSTEMS. International Journal of Modern Physics B, 2004, 18, 3597-3602.	1.0	2
146	Chaotic electron diffusion through stochastic webs enhances current flow in superlattices. Nature, 2004, 428, 726-730.	13.7	117
147	Use of stochastic web patterns to control electron transport in semiconductor superlattices. Physica D: Nonlinear Phenomena, 2004, 199, 166-172.	1.3	10
148	Resonance and current instabilities in AlN/GaN resonant tunnelling diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 752-755.	1.3	19
149	Probing the N-induced states in dilute GaAsN alloys by magneto-tunnelling. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 892-896.	1.3	0
150	Study of electron dynamics in n-type GaN using the Osaka free electron laser. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2004, 528, 623-626.	0.7	0
151	Magneto-photoluminescence of stacked self-assembled InAs/GaAs quantum dots. Physica B: Condensed Matter, 2004, 346-347, 428-431.	1.3	10
152	Nonequilibrium Green's function approach to resonant transport in semiconductor superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 717-721.	1.3	1
153	Light-emitting diodes based on GaMnAs/GaAs heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 1002-1006.	1.3	1
154	Model for breakdown of laminar flow of a quantum Hall fluid around a charged impurity: comparison with experiment. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 205-209.	1.3	1
155	Magneto-tunnelling spectroscopy of nitrogen clusters in Ga(AsN) alloys. IEE Proceedings: Optoelectronics, 2003, 150, 49.	0.8	4
156	Controlling the shape of InAs self-assembled quantum dots by thin GaAs capping layers. Journal of Crystal Growth, 2003, 251, 155-160.	0.7	32
157	Currentâ€“voltage instabilities in GaN/AlGaN resonant tunnelling structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2389-2392.	0.8	52
158	Floating gold in cryogenic oxygen. Nature, 2003, 422, 579-579.	13.7	70
159	Magneto-photoluminescence studies of the influence of substrate orientation on the growth of InAs/GaAs quantum dots. Journal of Crystal Growth, 2003, 251, 186-191.	0.7	0
160	Emission energy and polarization tuning of InAs/GaAs self-assembled quantum dots by growth interruption. Journal of Crystal Growth, 2003, 251, 192-195.	0.7	8
161	Strain relaxation in stacked InAs/GaAs quantum dots studied by Raman scattering. Applied Physics Letters, 2003, 83, 3069-3071.	1.5	36
162	Nonlinear hole transport through a submicron-size channel. Applied Physics Letters, 2003, 82, 925-927.	1.5	1

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163	Investigation of radiative recombination from Mn-related states in Ga1â^'xMnxAs. Applied Physics Letters, 2003, 83, 866-868.	1.5	5
164	Magnetic-field-induced recovery of resonant tunneling into a disordered quantum well subband. Physical Review B, 2003, 68, .	1.1	11
165	Probing the effective mass anisotropy ofÎ“electrons in a GaAs/(AlGa)As quantum well. Physical Review B, 2003, 67, .	1.1	4
166	Comment on â€œAlN/GaN double-barrier resonant tunneling diodes grown by rf-plasma-assisted molecular-beam epitaxyâ€•[Appl. Phys. Lett. 81, 1729 (2002)]. Applied Physics Letters, 2003, 83, 3626-3627.	1.5	37
167	Spatial mapping of the electron eigenfunctions in InAs self-assembled quantum dots by magnetotunnelling. Nanotechnology, 2003, 14, 16-19.	1.3	3
168	Dependence of quantum-dot formation on substrate orientation studied by magnetophotoluminescence. Applied Physics Letters, 2002, 81, 1480-1482.	1.5	12
169	Tailoring the electronic properties of GaAs/AlAs superlattices by InAs layer insertions. Applied Physics Letters, 2002, 81, 661-663.	1.5	36
170	Controlling the electron tunneling through InAs self-assembled dots. Journal of Applied Physics, 2002, 91, 3474-3476.	1.1	4
171	<title>Effective mass anisotropy of T-electrons in GaAs/AlGaAs quantum well with InAs layer</title>. , 2002, , .		0
172	Photoresponse spectra in p-i-n diodes containing quantum dots. Nanotechnology, 2002, 13, 94-96.	1.3	6
173	<title>Magneto-tunnelling spectroscopy of the electron states in the quantum well with embedded self assembled quantum dots: studies in magnetic field up to 28 T</title>. , 2002, , .		0
174	<title>Tunnel gaps in the two-dimensional electron system in a magnetic field</title>. , 2002, , .		0
175	<title>Escape of carriers photoexcited in self-organized InAs/GaAs quantum dots</title>. , 2002, , .		0
176	<title>Breakdown of the interger quantum Hall effect: a microscopic model with a hydronamical analogy</title>. , 2002, , .		0
177	Tunneling spectroscopy of mixed stable-chaotic electron dynamics in a quantum well. Physical Review B, 2002, 65, .	1.1	12
178	Study of electronâ€“hole generation and recombination in semiconductors using the Osaka free electron laser. Physica B: Condensed Matter, 2002, 314, 431-436.	1.3	21
179	Quantum Hall effect breakdown: can the bootstrap heating and inter-Landau-level scattering models be reconciled?. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 178-181.	1.3	6
180	Magnetic field induced linear Coulomb gap in tunnelling between disordered two-dimensional electron systems. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 300-303.	1.3	0

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